This listing of claims will replace all prior versions of claims in the application.

Claim 1. (currently amended) A method for forming a photoresist relief image on a substrate comprising:

(a) applying a coating layer of a chemically-amplified positive photoresist composition on a substrate, the photoresist composition comprising ~~(i)~~ a phenolic resin that comprises at least three distinct repeat units and (ii) one or more photoacid generator compounds,

wherein the one or more photoacid generator compound are present in a concentration of from 5 to 15 ~~5.0 to 15.0~~ weight percent based on weight of total solids of the photoresist composition, and

wherein the photoresist does not contain a blend of resins of different compositions;

(b) exposing the photoresist coating layer to EUV radiation to form a photoresist relief image.

Claims 2-6. (cancelled)

Claim 7. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are present in a concentration of at least about 6 weight percent based on weight of total solids of the photoresist composition.

Claim 8. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are present in a concentration of from 5 to 12 ~~5.0 to 12.0~~ weight percent based on weight of total solids of the photoresist composition.

Claim 9. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are present in a concentration of at least about 12 weight percent based on weight of total solids of the photoresist composition.

Claim 10. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are present in a concentration of from 11 to 15 weight percent based on weight of total solids of the photoresist composition.

Claim 11. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are ionic compounds.

Claim 12. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are non-ionic compounds.

Claim 13. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds are onium compounds, imidosulfonate compounds, N-sulfonyloxyimide compounds, sulfonate ester compounds, nitrobenzyl compounds, disulfone compounds, and/or halogenated non-ionic compounds, or mixtures thereof.

Claim 14. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds produce a halo-alkyl sulfonic acid upon exposure to activating radiation.

Claim 15. (currently amended) The method of claim 1 ~~or 2~~ wherein the one or more photoacid generator compounds produce a per-fluoro sulfonic acid upon exposure to activating radiation.

Claim 16. (currently amended) The method of claim 1 or 2 wherein the resin comprises a polymer that contains phenolic units.

Claim 17. (currently amended) The method of claim 1 ~~or 2~~ wherein the resin comprises a polymer ~~that contains phenolic and~~ photoacid-labile alkyl acrylate units.

Claim 18. (currently amended) The method of claim 1 ~~or 2~~ wherein the resin comprises ~~a polymer that contains~~ 1) phenolic units, 20 phenyl units, and 3) photoacid-labile alkyl acrylate units.

Claim 19. (currently amended) The method of claim 1 ~~or 2~~ wherein the resin comprises a polymer that contains acetal, ketal or ortho ester groups.

Claim 20. (currently amended) The method of claim 1 ~~or 2~~ wherein the photoresist resin component does not contain acetal, ketal or ortho ester groups.

Claim 21. (cancelled)

Claim 22. (new) A method for forming a photoresist relief image on a substrate comprising:

(a) applying a coating layer of a chemically-amplified positive photoresist composition on a substrate, the photoresist composition comprising (i) a phenolic resin that comprises at least three distinct repeat units and (ii) one or more photoacid generator compounds,

wherein the one or more photoacid generator compound are present in a concentration of from 11 to 15 weight percent based on weight of total solids of the photoresist composition, and

(b) exposing the photoresist coating layer to EUV radiation to form a photoresist relief image.

Claim 23. (new) The method of claim 22 wherein the one or more photoacid generator compounds are present in a concentration of at least about 12 weight percent based on weight of total solids of the photoresist composition